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			Complet if Known
Substitute for form 1449A/B/PTO	l	Application Number	Unknown
		Filing Date	December 11, 2001
INFORMATION DISCLOSURE		First Named Inventor	IZUO
STATEMENT BY APPI	LICANT	Group Art Unit	Unknown
-		Examiner Name	Unknown
(Use as many sheets as necess	<u>sary)</u>	Attorney Docket Number	401479/AOYAMA
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^{*} A concise statement of relevance is being submitted in lieu of a translation. 37 CFR 1.98(a)(3).

+ An English-language equivalent/patent, or an English-language abstract, or an English-language version of the search report or action by a foreign patent office in a counterpart foreign application indicating the degree of relevance found by the foreign office is being submitted in lieu of a concise explanation of relevance under 37 CFR 1.98(a)(3).